

/ Descriptions

TO-126F PNP Silicon PNP transistor in a TO-126F Plastic Package.

/ Features

High breakdown voltage, small reverse transfer capacitance and excellent high frequency characteristic.

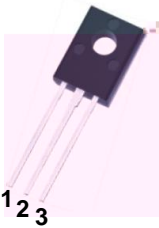
/ Applications

Ultrahigh-definition CRT display, video output applications.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Collector PIN 3 Base

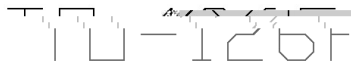
/ h_{FE} Classifications & Marking

h _{FE} Classifications Symbol	C	D	E	F
h _{FE} Range	40 80	60 120	100 200	160 320

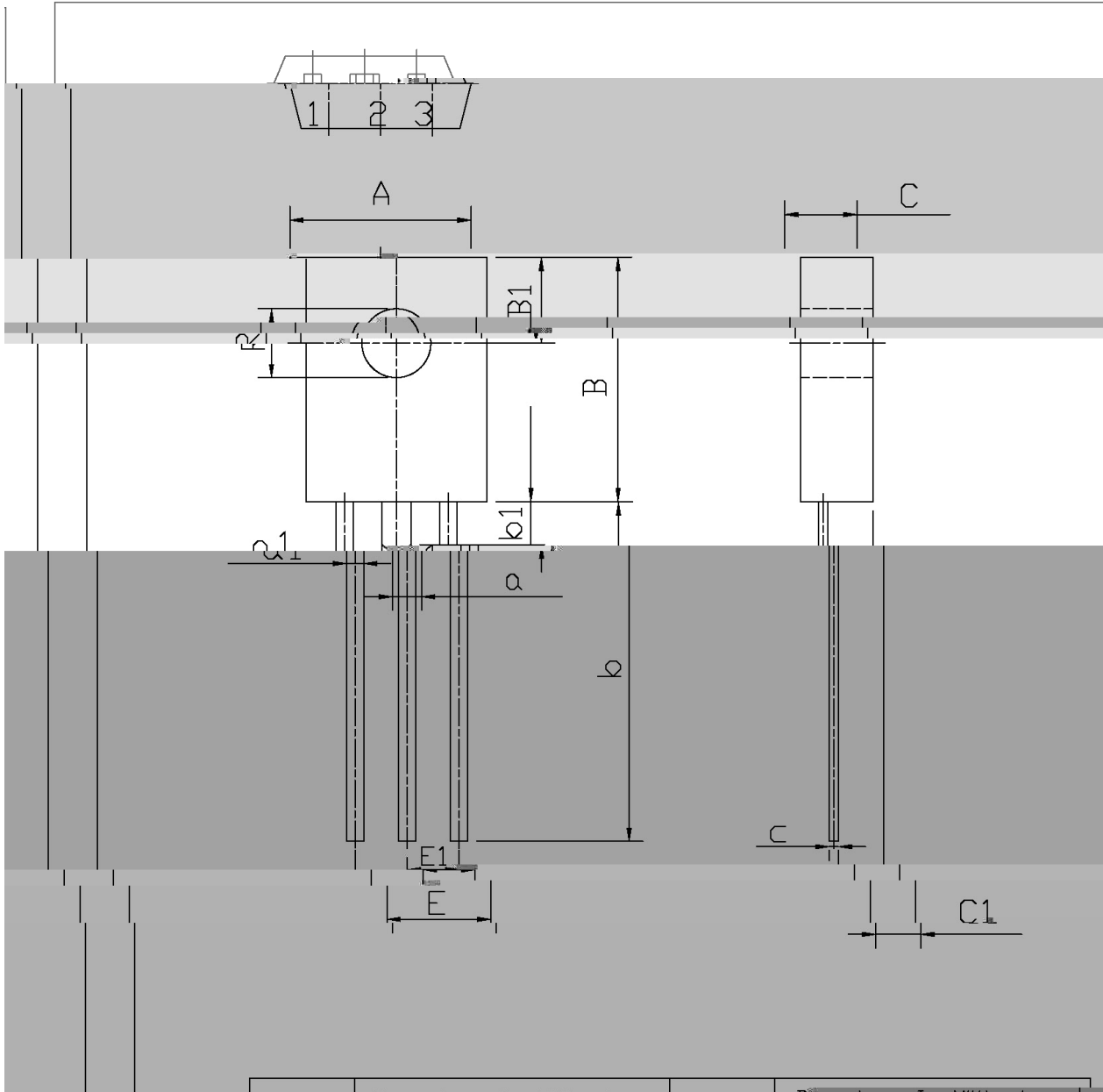
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-200	V
Collector to Emitter Voltage	V_{CEO}	-200	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mA
Collector Current – Continuous	I_{CP}	-200	mA
Collector Power Dissipation	P_C	1.2	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -10\text{ A}$ $I_E = 0$	-200			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0\text{ mA}$ $R_{BE} =$	-200			V

/ Package Dimensions

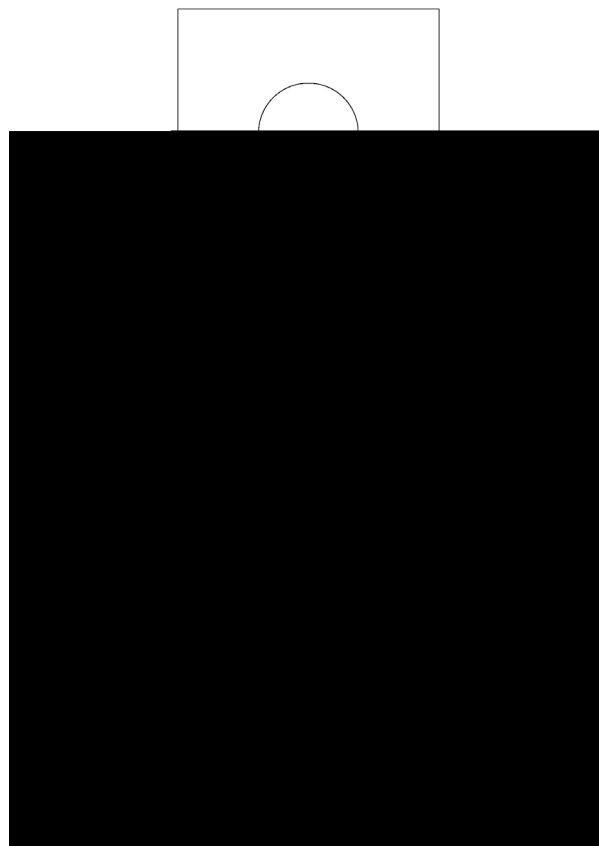


单位: mm



Symbol	Min	Max	Symbol	Min
A	7.8	8.2	a ₁	0.65
B	10.8	11.2	E	0.4

/ Marking Instructions



BR

A1380

C: h_{FE}

Note:

BR: Company Code

A1380: Product Type.

C: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.

2SA1380
Rev.E Mar.-2016

(